### **Wide Gap Optical Sensor**

### **OPB856Z**



#### Features:

- Designed for Industrial applications
- Threaded housing (M12 X 1 TH), Nut included
- Molded connectors mates with Molex 03-06-2023 plug.
- Emitter (White) and Senor (Black) housing color coded



#### Description:

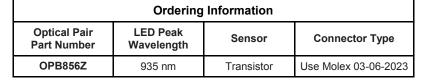
The **OPB856** emitter and sensor pair consists of an LED (935 nm) and a Phototransistor designed to operate efficiently with each other. They are mounted in a threaded (M12x1TH) color-coded housing. The LED (white) and the Phototransistor (black) are designed to easily panel mount in through a 0.4724" (12.0 mm) hole. A 12 mm nut is included for each housing. Both components is designed to electrically mate with a Molex (03-06-2023) connector.

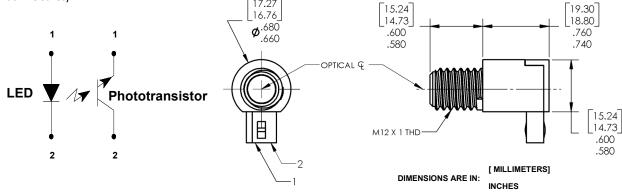
The OPB856 pair are designed to operate with separation distances between the LED and Phototransistor up to 12" (30.48 cm).

For Custom electrical, wire and cabling and connectors are available. Contact your local representative or OPTEK for more information.

### Applications:

- Non-contact interruptive object sensing
- Assembly line automation
- Machine automation
- Equipment security
- Machine safety





Housing	LED - White	Sensor - Black		
Plug	MOLEX 03-06-2023	MOLEX 03-06-2023		
Pin for Plug	Male MOLEX 02-06-6122	Female MOLEX 02-06-7104		

White Housing		Black Housing			
Pin#	LED	Pin#	Phototransistor		
1	Anode	1	Emitter		
2	Cathode	2	Collector		



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### **Electrical Specifications**

Absolute	e Maximum Ratings (T <sub>A</sub> = 25° C unles	s other	wise no	oted)				
Storage & Operating Temperature Range							-40° C to +85° C	
Lead	260° C							
Input Dio	de (See OP165 for additional information)							
Conti	40 mA							
Reverse Voltage							2 V	
Powe	er Dissipation <sup>(1)</sup>						100 mW	
Output Ph	ototransistor (See OP505 for additional inf	formatio	on)					
Collector-Emitter Voltage							30 V	
Emitter-Collector Voltage							5 V	
Power Dissipation <sup>(1)</sup>							100 mW	
Electrico	Il Characteristics (T <sub>A</sub> = 25° C unless ot	herwise	e noted	)				
SYMBOL	PARAMETER	MIN	ТҮР	MAX	UNITS	TEST CONDITIONS		
Input Dio	de (See OP165 for additional information)							
V <sub>F</sub>	Forward Voltage	-	-	1.7	V	I <sub>F</sub> = 20 mA		
I <sub>R</sub>	Reverse Current	-	-	100	μΑ	V <sub>R</sub> = 2 V		
Output P	hototransistor (See OP505 for addition	nal info	rmatior	า)		1		
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	30	-	-	V	Ι <sub>C</sub> = 100 μΑ		
V <sub>(BR)ECO</sub>	Emitter-Collector Breakdown Voltage	5	-	-	V	Ι <sub>Ε</sub> = 100 μΑ		
I <sub>CEO</sub>	Collector Dark Current	-	-	100	nA	V <sub>CE</sub> = 10 V, I <sub>F</sub> = 0, E <sub>E</sub> = 0		
Combine	d					1		
I <sub>C(ON)</sub>	On-State Collector Current <sup>(3)</sup>	1.8	-	-	mA	$V_{CE} = 5 \text{ V, } I_F = 20 \text{ mA, } d = 2'' (50.8 \text{ mm})^{(2)}$		

#### Notes:

- (1) Derate linearly 1.67 mW/°C above 25 ° C..
- (2) Distance between lenses along the optical axis is "d".
- (3) All parameters tested using pulse technique.

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# Normalized Collector Current vs. Distance between Emitter and Sensor

